# BLC10G27XS-551AVT

# Power LDMOS transistor

**AMPLEON** 

Rev. 1 — 20 September 2019

Product data sheet

# 1. Product profile

### 1.1 General description

550 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 2620 MHz to 2690 MHz.

#### Table 1. Typical performance

Typical RF performance at  $T_{case} = 25$  °C in an asymmetrical Doherty demo circuit.  $V_{DS} = 32$  V;  $I_{Dq} = 1000$  mA (main);  $V_{GS(amp)peak} = 0.85$  V, unless otherwise specified.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2620 to 2690	32	91	13.5	46	-31.3 <sup>[1]</sup>

<sup>[1]</sup> Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

### 1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 2620 MHz to 2690 MHz frequency range

# 2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain2 (peak)			0.7
2	drain1 (main)		7 2 1 6	2,7
3	gate1 (main)		5	
4	gate2 (peak)		3 4	3——5
5	source	[1]		4—
6	video decoupling (peak)			" <del>'</del> ¬
7	video decoupling (main)			1, 6 aaa-014884

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Packag	ckage					
	Name	ame Description					
BLC10G27XS-551AVT	-	air cavity plastic earless flanged package; 6 leads	SOT1258-4				

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
V <sub>GS(amp)main</sub>	main amplifier gate-source voltage		-6	+9	V
V <sub>GS(amp)peak</sub>	peak amplifier gate-source voltage		-6	+9	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C
T <sub>case</sub>	case temperature	operating [1]	-40	+125	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

# 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	V <sub>DS</sub> = 32 V; I <sub>Dq</sub> = 1000 mA (main); V <sub>GS(amp)peak</sub> = 0.885 V; T <sub>case</sub> = 80 °C		
		P <sub>L</sub> = 87 W	0.24	k/W
		P <sub>L</sub> = 110 W	0.22	k/W

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# 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice		<b>-</b>		1	
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.8 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 180 mA	1.6	2.0	2.4	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 32 V; I <sub>D</sub> = 1000 mA	-	2.2	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	34	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 9 V; V <sub>DS</sub> = 0 V	-	-	280	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 9.0 A	-	20.5	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $I_D = 6.3 \text{ A}$	-	72	108	mΩ
Peak dev	rice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3.8 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 380 mA	1.6	2.0	2.4	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 32 V; I <sub>D</sub> = 1900 mA	-	2.2	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	57	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 9 V; V <sub>DS</sub> = 0 V	-	-	280	nA
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 19.0 A	-	39.0	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $I_D = 13.3 \text{ A}$	-	37	62	mΩ

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH;  $f_1$  = 2622.5 MHz;  $f_2$  = 2687.5 MHz; RF performance at  $V_{DS}$  = 32 V;  $I_{Dq}$  = 1000 mA (main);  $V_{GS(amp)peak}$  = 0.9 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2620 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L(AV)</sub> = 91 W	12	13	-	dB
RLin	input return loss	P <sub>L(AV)</sub> = 91 W	-	-14	-10	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 91 W	41	45	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 91 W	-	-29	-24	dBc

#### Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f = 2687.5 MHz; RF performance at  $V_{DS} = 32$  V;  $I_{Dq} = 1000$  mA (main);  $V_{GS(amp)peak} = 0.9$  V;  $T_{case} = 25$  °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at a frequency of 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PARO	output peak-to-average ratio	P <sub>L(AV)</sub> = 145 W	5.9	6.4	-	dB
$P_{L(M)}$	peak output power	P <sub>L(AV)</sub> = 145 W	553	628	-	W

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# 7. Test information

### 7.1 Ruggedness in Doherty operation

The BLC10G27XS-551AVT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 32 V;  $I_{Dq}$  = 1000 mA;  $V_{GS(amp)peak}$  = 0.885 V; f = 2620 MHz;  $P_{L}$  = 230 W (5 dB OBO); 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on the CCDF.

# 7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dq} = 900$  mA (main);  $V_{DS} = 32$  V; pulsed CW ( $t_p = 100 \ \mu s$ ;  $\delta = 10 \ \%$ ).

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]			
(MHz)	<b>(</b> Ω <b>)</b>	<b>(</b> Ω <b>)</b>	(W)	(%)	(dB)			
Maximum	Maximum power load							
2500	1.1 – j5.2	1.8 – j4.4	306	59.3	13.9			
2600	1.6 – j5.8	1.9 – j4.5	301	60.0	14.1			
2690	2.5 – j6.5	2.0 - j4.3	298	60.2	14.2			
Maximum	drain efficiency	load						
2500	1.2 – j5.4	3.9 – j4.5	223	66.7	15.7			
2600	1.7 – j6.0	3.8 – j3.3	213	66.4	15.9			
2690	2.8 – j6.6	3.1 – j3.0	218	66.1	15.8			

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

Table 10. Typical impedance of peak device

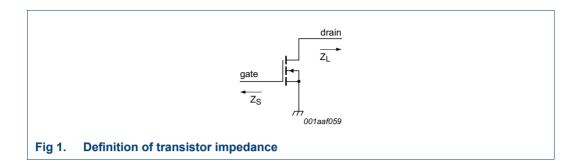
Measured load-pull data of peak device;  $I_{Dq}$  = 1900 mA (peak);  $V_{DS}$  = 32 V; pulsed CW ( $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %).

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	<b>(Ω)</b>	(Ω)	(W)	(%)	(dB)
Maximum	n power load				
2500	1.1 – j5.5	2.9 – j4.8	560	56.8	12.7
2600	1.5 – j6.3	2.9 – j4.3	553	57.2	13.0
2690	2.5 – j7.3	2.7 – j4.2	544	55.7	13.0
Maximum	n drain efficiency	load			
2500	1.0 – j5.5	4.1 – j3.0	469	56.7	14.0
2600	1.6 – j6.3	3.4 – j2.4	447	56.5	14.1
2690	2.6 – j7.4	2.6 – j2.6	442	56.5	14.2

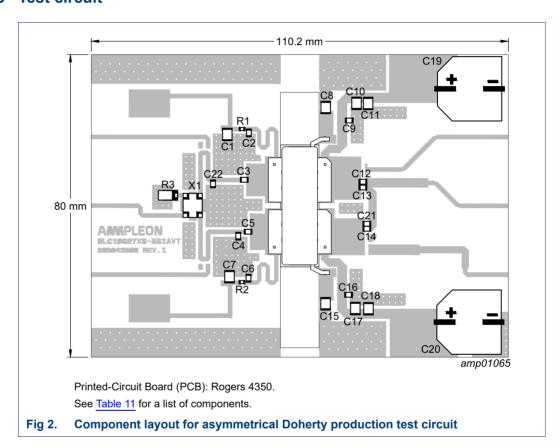
<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

<sup>[2]</sup> At 3 dB gain compression.

<sup>[2]</sup> At 3 dB gain compression.



### 7.3 Test circuit



**Table 11.** List of components For test circuit see Figure 2.

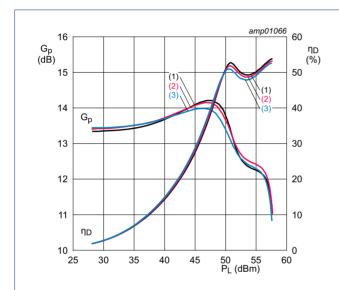
Component Description Value Remarks C1, C7, C8, C10, C11, multilayer ceramic chip capacitor 10 μF, 100 V Murata: 1210 C15, C17, C18 C2, C3, C5, C6, C9, C16 multilayer ceramic chip capacitor 6.8 pF Murata: HiQ 0805 C4 ATC 800A/8800B multilayer ceramic chip capacitor 0.2 pF C14, C21 multilayer ceramic chip capacitor 2.7 pF Murata: HiQ 0805 C22 multilayer ceramic chip capacitor 0.3 pF ATC 800A/8800B C12, C13 multilayer ceramic chip capacitor 3.6 pF Murata: HiQ 0805 C19, C20 multilayer ceramic chip capacitor 470 μF, 63 V EEVFK1J471M

**Table 11.** List of components ...continued For test circuit see Figure 2.

Component	Description	Value	Remarks
R1, R2	resistor	4.7 Ω, 1 %	SMD 0805
R3	resistor	50 Ω, 16 W	Anaren: C16A50Z4
X1	hybrid coupler	2 dB, 90°	Anaren: Xinger III, X3C25P1-02S

# 7.4 Graphical data

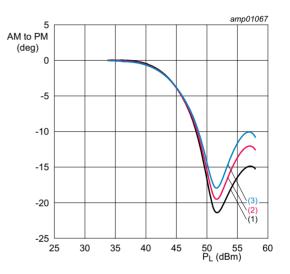
#### 7.4.1 Pulsed CW



 $V_{DS}$  = 32 V;  $I_{Dq}$  = 1000 mA;  $V_{GS(amp)peak}$  = 0.885 V;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values



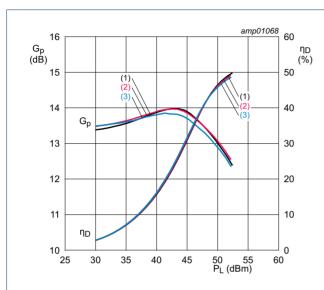
 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 4. Normalized AM to PM as a function of output power; typical values

#### 7.4.2 1-Carrier W-CDMA

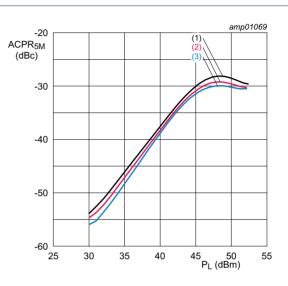
Test signal: 3GPP test model 1; 1 to 64 DPCH (100 % clipping); PAR = 9.9 dB at 0.01 % probability on CCDF per carrier.



 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

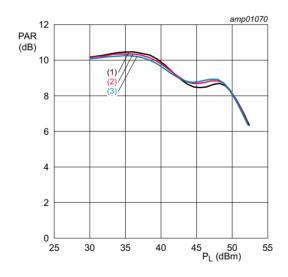
Power gain and drain efficiency as function of Fig 5. output power; typical values



 $V_{DS}$  = 32 V;  $I_{Dq}$  = 1000 mA;  $V_{GS(amp)peak}$  = 0.885 V.

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Adjacent channel power ratio (5 MHz) as a Fig 6. function of output power; typical values



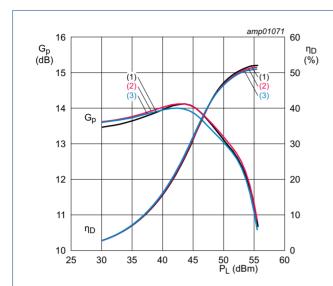
 $V_{DS}$  = 32 V;  $I_{Dq}$  = 1000 mA;  $V_{GS(amp)peak}$  = 0.885 V.

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Peak-to-average power ratio as a function of output power; typical values

#### 7.4.3 1-Carrier LTE

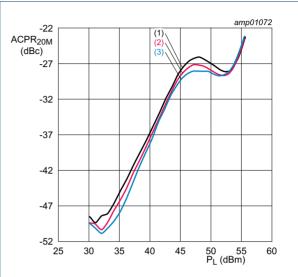
Test signal: 1-carrier LTE 10 MHz; PAR = 6.8 dB at 0.01 % probability on CCDF.



 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 8. Power gain and drain efficiency as function of output power; typical values

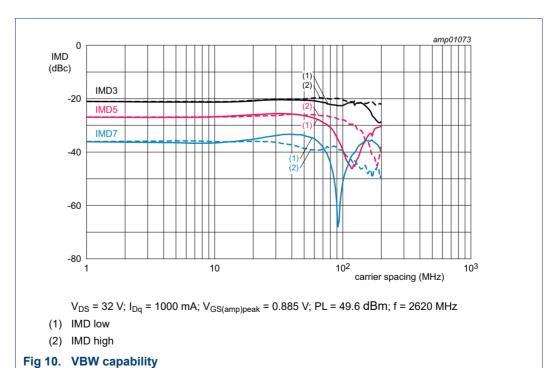


 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

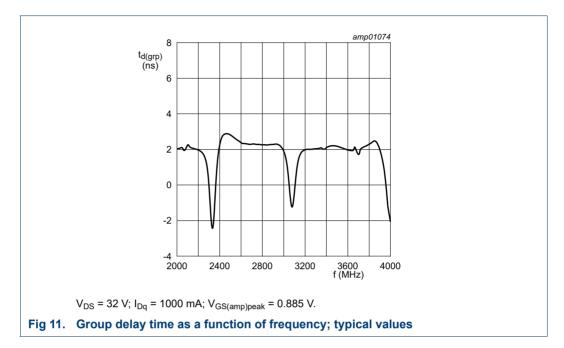
Fig 9. Adjacent channel power ratio (20 MHz) as a function of output power; typical values

# 7.4.4 2-Tone VBW



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# 7.4.5 Group delay



# 8. Package outline

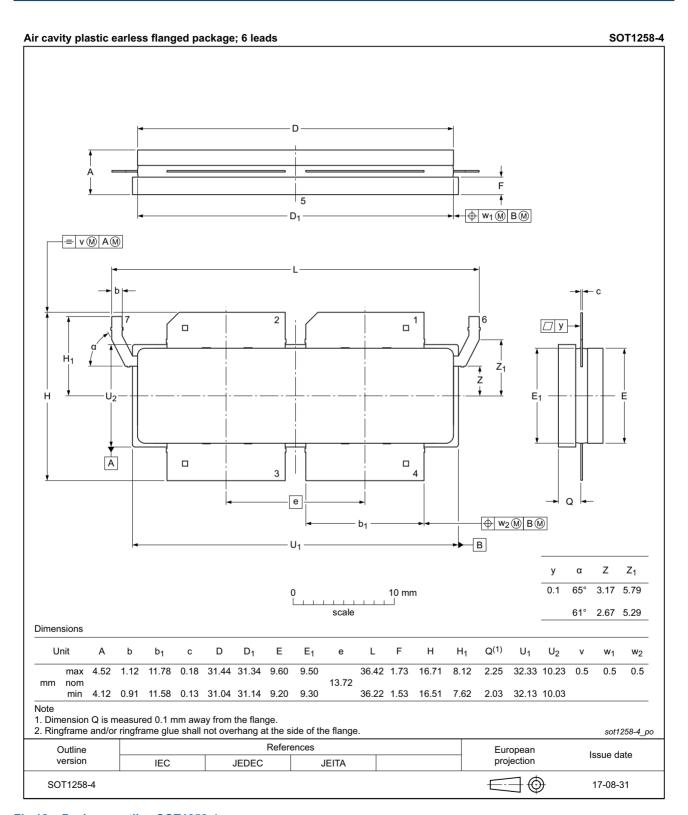


Fig 12. Package outline SOT1258-4

# 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C3 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of 1000 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

# 10. Abbreviations

Table 13. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
AM	Amplitude Modulation
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LTE	Long Term Evolution
MTF	Median Time to Failure
ОВО	Output Back Off
PAR	Peak-to-Average Ratio
PM	Phase Modulation
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

# 11. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC10G27XS-551AVT v.1	20190920	Product data sheet	-	-

BLC10G27XS-551AVT

# 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# 14. Contents

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